

Supporting Information

Self-Assembled Polypyrrole Nanotubes/MoS₂ Quantum Dots for High Performance Solid State Flexible Symmetric Supercapacitor

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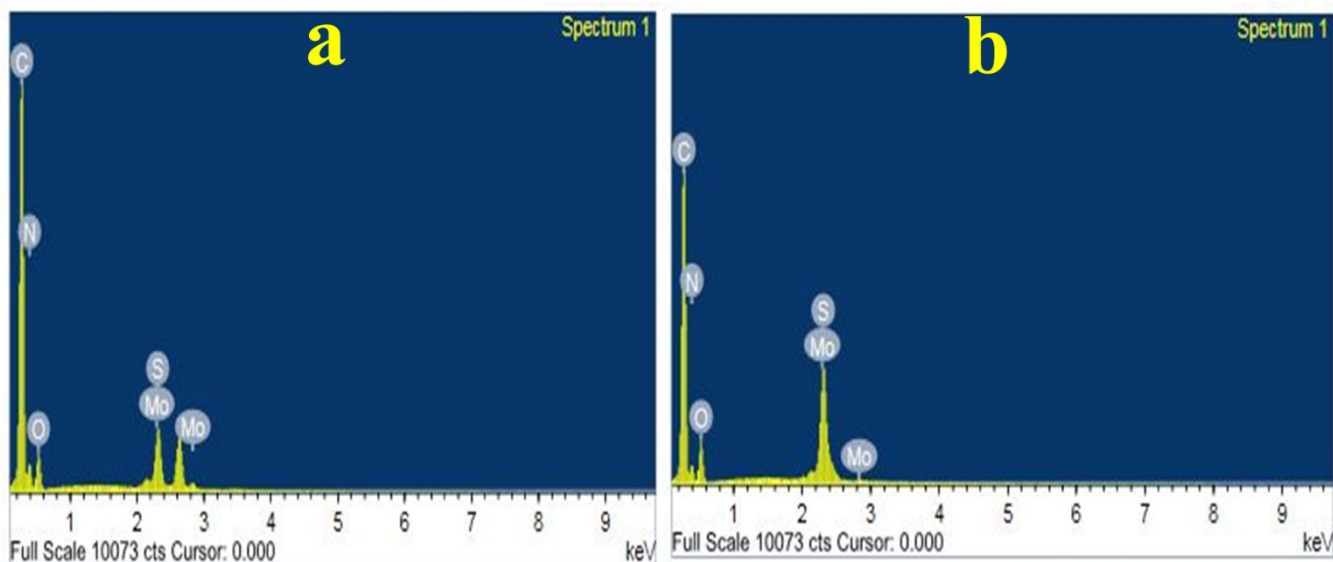


Figure S1. The EDAX pattern of (g) PNTs, (h) PNTs/MoS₂ and (i) CS-PNTs/MoS₂ nanocomposites.

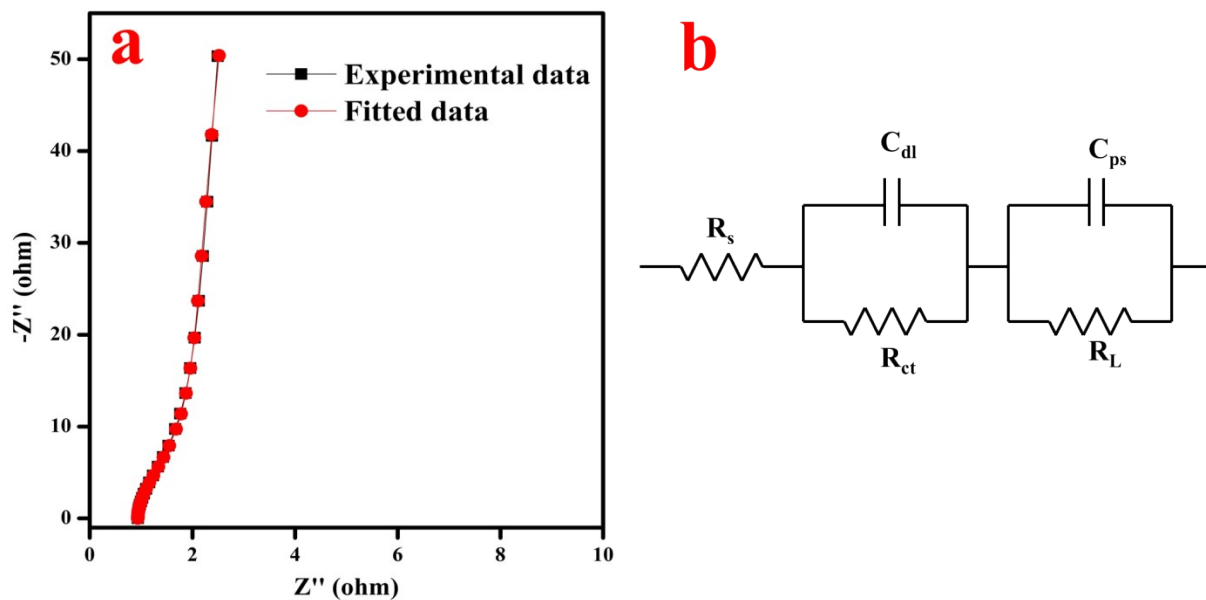


Figure S2. (a) The fitted Nyquist plot with the experimental plot. (b) Equivalent circuit.

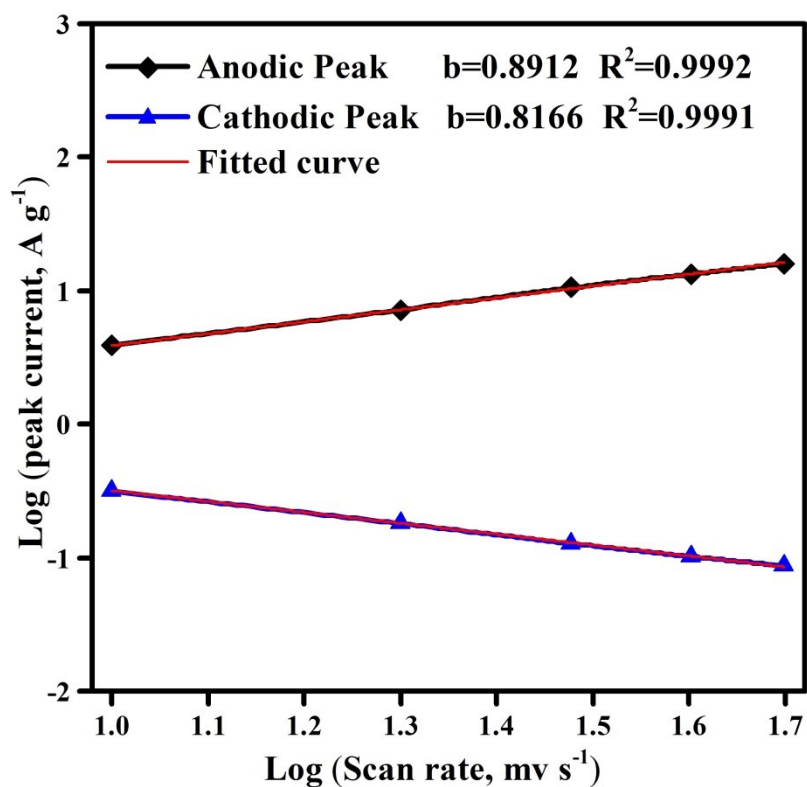


Figure S3. Dependence of anodic and cathodic peak current on the scan rates

Table S1. Specific capacity of different samples from CV and GCD at scan rate of 50 mV/s and current density of 1 A/g.

Samples	C _{sp} from GCD (C/g)	C _{sp} from GCD (C/g)
PNTs	437	255
PNTs/MoS ₂	646	520
CS-PNTs/MoS ₂	856	759

Table S2. Specific capacity of CS-PNTs/MoS₂ //CS-PNTs/MoS₂ SSC device for different current density.

CV		GCD	
Scan rate (mV/s)	C _{sp} (C/g)	Current density (A/g)	C _{sp} (C/g)
10	442	1	437
20	418	2	371
30	393	4	183
40	342	5	170
50	307	7	142
		10	102

Table S3. Impedance parameter obtained from equivalent circuit for Nyquist plot of CS-PNTs/MoS₂ //CS-PNTs/MoS₂ SSC device.

Parameters	Values
R _s	0.9388
C _{dl}	7.239E-5
R _{ct}	1.18
Z _w	0.637
C _{ps}	0.0048